

AN ORGANOMETALLIC COMPOSITION FOR FORMING A METAL ALLOY
PATTERN AND A METHOD OF FORMING SUCH A PATTERN USING THE
COMPOSITION

BACKGROUND OF THE INVENTION

[0001] This non-provisional application claims priority under 35 U.S.C. § 119(a) on Patent Application No. 2002-73498 filed in Korea on November 25, 2002, which is herein incorporated by reference.

FIELD OF THE INVENTION

[0002] The present invention relates to a composition of organometallic compounds and to a method of forming a metal alloy pattern using the same, and more specifically, to a composition of organometallic compounds comprising organometallic compound (I) containing Ag, organometallic compound (II) containing Au, Pd or Ru, and organometallic compound (III) containing Ti, Ta, Cr, Mo, Ru, Ni, Pd, Cu, Au or Al, wherein the metal components of the organometallic compounds (II) and (III), respectively, are present in an amount of 0.01~10mol% of based on the amount of Ag in the

organometallic compound (I). The present invention is also directed to a method of forming a metal alloy pattern using the same.

BACKGROUND OF THE INVENTION

[0003]In the production of electronic devices such as integrated circuits or liquid crystal displays, microlithography techniques have been used to form a patterned film of materials such as metal, which have desired electrical properties, on a certain substrate including a crystallized silicon wafer, a glass substrate, and the like. Microlithography comprises several steps including that of: forming a base layer of metallic materials on a substrate through chemical vapor deposition, plasma deposition or electroplating; applying a photoresist layer on the metal layer; exposing the photoresist layer under a photomask to light; developing the photoresist layer to provide a patterned photoresist layer; and etching the metal layer beneath the patterned photoresist layer by, for example, reactive etching to provide the metal wiring of a micro-pattern. Such multiple processes of microlithography, in addition to requiring the use of expensive photoresists and chemical etching material, make it undesirable in the light of cost as

well as the protection of the environment. Moreover, many of the processes should be carried out under high temperatures and/or high pressures, and in such condition, diffusion of metallic vapor into the substrate is likely to occur, resulting in a deterioration of the final electronic devices. Recently, in the field of flexible display and TFT-LCD, demand has increased for requiring improved techniques of forming a high quality gate insulating film and a low resistance source/drain electrode area, and accordingly, diversified studies have been made to provide a more simplified method of forming a metal pattern.

[0004]For example, Japanese Laid-Open Publication No. 62-263973 discloses a patterning method, wherein an electron beam is irradiated on a thin film of organometallic compounds to form a metal pattern. In this method, an excessive amount of electron beam is necessary and thus mass-production of the metal pattern becomes difficult. Also, there is concerns about ununiformity of the metal pattern.

[0005]In US Patent No. 5,064,685, an ink-containing organometallic compound is coated on a substrate, and, by exposure to a laser beam, the resulting coat is allowed to undergo thermal degradation to provide a

patterned metal film. However, this method has a serious shortcoming in that the substrate should be subjected to high temperature conditions, and therefore a pattern of silver or silver alloy cannot be produced by this process.

[0006] On the other hand, US Patent Nos. 5,534,312 and 6,348,239 describe that a metal pattern can be obtained by coating a substrate with an organometallic complex synthesized by bonding one or more photosensitive organic ligands to one or more metal atoms, and exposing the coating to electromagnetic radiation, wherein any photosensitive resin needs not to be used. When exposed to electromagnetic radiation, the organometallic complex goes through a photochemical reaction, resulting in the dissociation of the organic ligands from the central metal atom. The remaining metal atoms then react with adjacent metal atoms and/or atmospheric oxygen atoms to form an oxidized metal pattern. However, there are several problems with ligand dissociation through photochemical reaction. Typically, the ligand dissociation rate is so low that a large amount of time is required to complete the patterning, and ligand contamination is inevitable. In addition, for improving the reflectivity of the

oxidized metal pattern, heat treatment at 200°C or more under a mixed gas stream of H₂/N₂ is required, and such treatment is not applicable to silver and silver alloys.

[0007] Thus, there remains a strong demand in the art to develop a method of producing a reflective film of silver or silver alloy under mild conditions while improving heat-resistance, adhesiveness and stability to discoloration caused by atmospheric oxygen.

[0008] At the same time, it should be realized that Silver is difficult to use in the production of a patterned film for numerous reasons: Silver is highly reactive with non-metallic elements, so it readily becomes discolored into a black or milky color, for example, by forming Ag₂S or AgCl with sulfur or chloride in the atmosphere. In addition, silver is vulnerable to heat, so, in the case of producing a reflective film for LCD's by the use of silver, the process temperature should be controlled to prevent diffusion of the outer layer of the silver film. A reflective film comprising silver has a further problem in that yellow, reflected light is too strong at short wavelengths (i.e., 450nm or less), and this yellowing problem gradually becomes severe. Therefore, silver has been seldom regarded as a useful material in the

production of LCD's or PDA's.

[0009]In order to overcome these shortcomings of silver, Japanese Laid-Open Publication Nos. 01-221980 and 01-226765 disclose silver alloys containing 0.1~3.0wt% of Pt, Pd or Rb and 0.1~3.0wt% of at least one of Cu, Ti, Cr, Ta, Ni, Mo and Al. These alloys, however, are produced as a film on a substrate by sputtering so that microlithography processing is essential for obtaining a desired pattern, which is problematic in light of the complexity and expenses as described above.

SUMMARY OF THE INVENTION

[0010]One of the features of the present invention is to provide a ternary organometallic composition, which includes a first organometallic compound containing Ag, a second organometallic compound containing at least one of Au, Pd or Ru, and a third organometallic compound containing at least one of Ti, Ta, Cr, Mo, Ru, Ni, Pd, Cu, Au or Al.

[0011]The present invention also defines a method of forming a metal alloy pattern using the ternary organometallic composition.

[0012]All of the above features and other features of the present invention

will be successfully achieved as described in the following description.

[0013] Further scope of applicability of the present invention will become apparent from the detailed description given hereinafter. However, it should be understood that the detailed description and specific examples, while indicating preferred embodiments of the invention, are given by way of illustration only, since various changes and modifications within the spirit and scope of the invention will become apparent to those skilled in the art from this detailed description.

DETAILED DESCRIPTION OF THE INVENTION

[0014] The inventive composition of organometallic compounds as defined by the present invention comprises organometallic compound (I) of Formula 1 containing Ag, organometallic compound (II) of Formula 2 containing Au, Pd or Ru, and organometallic compound (III) of Formula 3 containing Ti, Ta, Cr, Mo, Ru, Ni, Pd, Cu, Au or Al:

Formula 1



wherein,

L is a neutral metallic ligand, which contains 1~20 carbon atoms and a donor selected from the group consisting of N, P, O, S and As;

X is an anion selected from the group consisting of F⁻, Cl⁻, Br⁻, I⁻, alkoxide, hydroxy, cyano(CN⁻), nitro(NO₂⁻), nitrate(NO₃⁻), nitroxyl, azide, thiocyanate, isothiocyanate, tetraalkylborate, tetrahaloborate, hexafluorophosphate(PF₆⁻), triflate(CF₃SO₃⁻), tosylate(Ts⁻), sulfate(SO₄²⁻), carbonate(CO₃²⁻), carboxylate, diketonate and alkyl anion;

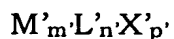
m is an integer from 1 to 10;

n is an integer from 0 to 40, provided that each L is the same or different in the case where n is 2 or higher, and provided that L functions as a ligand connecting Ag atoms in the case where m is 2 or higher;

p is an integer from 0 to 40, provided that each X is the same or different in the case where p is 2 or higher; and

both n and p are not zero at the same time.

Formula 2



wherein,

M' is Au, Pd or Ru;

L' is a neutral ligand containing 1~20 carbon atoms, which is selected from the group consisting of amine compounds, phosphine compounds, phosphite compounds, phosphineoxide compounds, arsine compounds, thiol compounds, carbonyl compounds, alkenes, alkynes and arene;

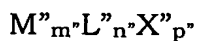
X' is an anion selected from the group consisting of, F⁻, Cl⁻, Br⁻, I⁻, alkoxide, hydroxy, cyano(CN⁻), nitro(NO₂⁻), nitrate(NO₃⁻), nitroxyl, azide, thiocyanate, isothiocyanate, tetraalkylborate, tetrahaloborate, hexafluorophosphate(PF₆⁻), triflate(CF₃SO₃⁻), tosylate(Ts⁻), sulfate(SO₄²⁻), carbonate(CO₃²⁻), carboxylate, diketone and alkyl anion;

m' is an integer from 1 to 10;

n' is an integer from 0 to 40, provided that each L' is the same or different in the case where n' is 2 or higher, and provided that L' functions as a ligand connecting metal atoms in the case where m' is 2 or higher;

p' is an integer from 0 to 40, provided that each X' is the same or different in the case where p' is 2 or higher; and

both p' and n' are not zero at the same time; and

Formula 3

wherein,

M'' is Ti, Ta, Cr, Mo, Ru(provided that M' in Formula 2 is not Ru), Ni, Pd(provided that M' in Formula 2 is not Pd), Cu, Au(provided that M' in Formula 2 is not Au) or Al;

L'' is a neutral ligand containing 1~20 carbon atoms, which is selected from the group consisting of amine compounds, phosphine compounds, phosphite compounds, phosphineoxide compounds, arsine compounds, thiol compounds, carbonyl compounds, alkenes, alkynes and arene;

X'' is an anion selected from the group consisting of F⁻, Cl⁻, Br⁻, I⁻, alkoxide, hydroxy, cyano(CN⁻), nitro(NO₂⁻), nitrate(NO₃⁻), nitroxyl, azide, thiocyanate, isothiocyanate, tetraalkylborate, tetrahaloborate, hexafluorophosphate(PF₆⁻), triflate(CF₃SO₃⁻), tosylate(Ts⁻), sulfate(SO₄²⁻), carbonate(CO₃²⁻), carboxylate, diketonate and alkyl anion;

m'' is an integer from 1 to 10;

n'' is an integer from 0 to 40, provided that each L'' is the same or

different in the case where n'' is 2 or higher, and provided that L'' functions as a ligand connecting metal atoms in the case where m'' is 2 or higher; and

p'' is an integer from 0 to 40, provided that each X'' is the same or different in the case where p'' is 2 or higher; and

both p'' and n are not zero at the same time.

[0015]In the organometallic compounds represented by Formulas 1~3, the number of ligand varies according to the kind and oxidation number of the metal atom and it can range from 0 to 6 for every metal atom. The number of anions can also range from 0 to 6 for every metal atom.

[0016]In Formulas 1~3, each of L , L' and L'' represents a neutral ligand bonded to metal atom(s) and, independently, is selected from the group consisting of amine compounds, phosphine compounds, phosphite compounds, phosphineoxide compounds, arsine compounds, thiol compounds, carbonyl compounds, alkenes, alkynes and arenes.

[0017]In Formulas 1~3, each of X , X' and X'' represents an anion which makes the corresponding organometallic compound electrically neutral and may or may not be coordinated to the metal atom(s).

[0018]Preferable examples of the organometallic compound of Formula 1

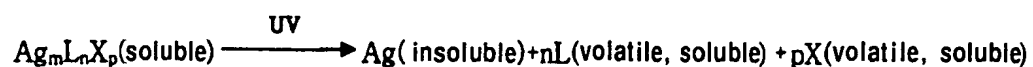
includes, but are not limited to, $\text{Ag}(\text{NO}_2)(\text{PrNH}_2)_n$, $\text{Ag}(\text{NO}_3)(\text{PrNH}_2)_n$, $\text{Ag}(\text{NO}_2)(\text{BuNH}_2)_n$ and $\text{Ag}(\text{NO}_3)(\text{BuNH}_2)_n$. Preferable examples of the organometallic compound of formula 2 includes, but are not limited to, $\text{AuPrNH}_2(\text{CN})$, palladium acetate $((\text{CH}_3\text{CO}_2)_2\text{Pd})$ and dicarbonylcyclopentadienyl ruthenium(II) dimer $((\text{C}_5\text{H}_5\text{Ru}(\text{CO})_2)_2)$. Preferable examples of the organometallic compound of Formula 3 includes, but are not limited to, $\text{AuPrNH}_2(\text{CN})$, palladium acetate $((\text{CH}_3\text{CO}_2)_2\text{Pd})$, dicarbonylcyclopentadienyl ruthenium(II) dimer $((\text{C}_5\text{H}_5\text{Ru}(\text{CO})_2)_2)$, copper(II) 2-ethylhexanoate $(([\text{CH}_3(\text{CH}_2)_3\text{CH}(\text{C}_2\text{H}_5)\text{CO}_2]_2\text{Cu})$ and titanium(IV) isopropoxide $(\text{Ti}[\text{OCH}(\text{CH}_3)_2]_4)$.

[0019] In the present invention, the metal component (represented by M') of the compound of Formula 2 is different from that (represented by M'') of the compound of Formula 3.

[0020] In the compound of Formula 1, the organic ligand (represented by L) is so sensitive to light that it becomes readily dissociated from the central metal atom and is decomposed according to Reaction Formula (i) upon exposure to light. Thus it is possible to obtain a patterned metal film without performing the laborious procedure of applying and etching the

photoresist film as defined in the prior art.

Reaction Formula (i)



[0021] In the present invention, the organometallic compounds of Formulas 2 and 3 need not have photosensitivity. Probably, it is believed that the organometallic compounds of Formulas 2 and 3, being mixed uniformly in the composition, are captured between the organometallic compound of Formula 1, and then they decompose during a subsequent annealing process or decompose by being deprived of electrons when the Ag-containing compound of Formula 1 is reduced upon irradiation. Therefore, in the inventive ternary composition of organometallic compounds, the amount of the compounds of Formulas 2 and 3 should be determined based on the Ag content of the composition. That is, the compounds of Formulas 2 and 3 are added to the compound of Formula 1 so that metal components provided by the compounds of Formulas 2 and 3, respectively, are present in an amount of 0.01~10mol%, more preferably 0.05~1mol% based on the mole amount of Ag provided by the compound of Formula 1. Where the metal component provided by the compound of Formula 2 or 3 exceeds 10mol%,

the results are not satisfactory because the specific resistance increases and the photoreaction velocity decreases. On the other hand, where it is less than 0.01mol%, there is little improvement in the adhesiveness or chemical stability of the final metal alloy pattern.

[0022]A method of forming a metal alloy pattern according to the present invention comprises the steps of: (i) dissolving the inventive composition of organometallic compounds in an organic solvent to produce a coating solution; (ii) coating a substrate with the coating solution to form a coating film; (iii) exposing the coating film to a light source using a photomask having a desired pattern; and (iv) developing the exposed film. As used herein, "metal alloy" is a term that can include not only a substantially pure metal alloy but also an oxide thereof.

[0023]In step (i), the organic solvent can be exemplified by, but is not limited to, a nitrile-based solvent such as acetonitrile, propionitrile, pentanenitrile, hexanenitrile, heptanenitrile and isobutylnitrile; an aliphatic hydrocarbon solvent such as hexane, heptane, octane and dodecane; an aromatic hydrocarbon solvent such as anisole, mesitylene and xylene; a ketone-based solvent such as methyl isobutyl ketone, 1-methyl-2-

pyrrolidinone, cyclohexanone and acetone; an ether-based solvent such as tetrahydrofuran, diisobutyl ether and isopropyl ether; an acetate-based solvent such as ethyl acetate, butyl acetate and propylene glycol methyl ether acetate; an alcohol-based solvent such as isopropyl alcohol, butyl alcohol, hexyl alcohol and octyl alcohol; and mixtures thereof.

[0024]In step (ii), the substrate can be made of inorganic materials such as silicon and glass; organic materials such as plastic; or composite materials comprising organic and inorganic matter.

[0025]In the present invention, coating of the substrate with the coating solution can be accomplished, for example, through spin coating, roll coating, dip coating, spray coating, flow coating or screen printing, while spin coating is most preferred.

[0026]In step (iii), the coating film thus formed is exposed to electromagnetic radiation. The light source for the electromagnetic radiation is not particularly limited, but UV light is most preferred.

[0027]During the exposure, the compound of Formula 1, in the unmasked portion of the coating film, undergoes a photochemical reaction as described in Reaction Formula (i), resulting in the transformation into a metal alloy or

an oxide thereof depending on the atmosphere of the exposure process. More specifically, when the organometallic compound is irradiated, the ligand bonded to the metal atom is dissociated and thus adjacent organometallic compounds become more unstable and consequently are converted into metal or metal oxide depending on the atmosphere. Although it varies with the type of metals and ligand, generally the photochemical reaction of organometallic compounds is as follows: through (a) metal to ligand charge transfer; (b) ligand to metal charge transfer; (c) d-d excite state; or (d) intramolecular charge transfer, whereby the bonds between metals and ligands become unstable and are broken. And as a result of such photochemical reactions, a solubility difference is created between exposed portions and unexposed portions of the coating film.

[0028]In step (iv), developing is accomplished either with a solvent used for the preparation of the coating solution in step (i), wherein a single solvent or a mixed solvent can be used according to the desired dissolution rate, or with any solvent typically used in semiconductor processes, such as tetramethylammoniumhydroxide(TMAH). For the purpose of improving clarity of the final pattern, two or more developing solvents can be used

alternatively.

[0029]In the present invention, the exposure and development steps can be performed in a vacuum or in an atmosphere of air, O₂, H₂, N₂, Ar or a mixed gas thereof. These steps are also performed at room temperature or at a temperature below the thermal decomposition temperature of the organometallic compounds.

[0030]After development, the obtained pattern may undergo a chemical reaction such as reduction or oxidation so as to obtain the metal or metal oxide. For obtaining pure metal, reduction is preferred and for obtaining the metal oxide, oxidation is preferred. The reduction or oxidation can be performed in a vacuum or in an atmosphere of air, O₂, H₂, N₂, Ar or a mixed gas thereof. In the reduction step any organic or inorganic reducing agent can be used. Preferable organic reducing agents are exemplified by, but are not limited to, hydrazines, silanes, amines, and derivatives thereof. Preferable inorganic reducing agents can be exemplified by, but are not limited to, metal hydrides such as NaBH₄ and LiAlH₄. These organic and inorganic reducing agents can be used themselves or as a solution in a proper solvent, and thus the reduction can be performed in gas-phase or

liquid-phase. Meanwhile, oxidation can be accomplished by the use of any organic or inorganic oxidant. Non-limiting examples of the organic oxidant include N-oxides such as trimethylamine N-oxide and pyridine N-oxide; peroxides such as bis(trimethylsilyl)peroxide; perbenzoic acid; O₃; and O₂. Inorganic oxidants such as H₂O₂, H₂SO₄ and HNO₃ can also be used.

[0031]The inventive method of forming a metal alloy pattern may further comprise an annealing step if necessary. Annealing is performed at a temperature of 300°C or lower, preferably 200°C or lower, in vacuum or in an atmosphere of air, N₂ gas or a N₂/H₂ mixed gas. In contrast with the prior art, annealing of the coating film can be accomplished at a relatively low temperature of 300°C or lower, so a desired metal alloy pattern can be formed even on a heat-labile substrate such as glass or a plastic plate.

[0032]According to the present invention, multilayer films of metal alloy can be obtained which may be employed in most electronic devices. In multilayer films, each layer can have the same or different metal composition. Such a multilayer film can be obtained by repeating all the steps of the inventive method of forming a metal alloy pattern, including steps (i) through (iii) and, optionally, the additional step of reduction,

oxidation and/or annealing as described above.

[0033]The inventive method of forming a metal alloy pattern may be applied to making a reflective film for LCD's and metal wiring (gate, source, drain electrode) for flexible displays or flat panel displays, and further to CMP-free damascene processing and PR-free ITO film deposition.

[0034]The present invention can be more clearly understood with referring to the following examples. It should be understood that the following examples are not intended to restrict the scope of the present invention in any manner.

Production examples of photosensitive organometallic coordination
compounds

[0035]Synthesis of $\text{Ag}(\text{NH}_2\text{Pr})_n(\text{NO}_2)$ mixture($n = 1, 2, 3$ and 4)

[0036]The synthesis is performed in a N_2 atmosphere while excluding atmospheric moisture and oxygen by Schlenk technique or Glove box. In a 50ml round bottom Schlenk flask, 3.08g(20.0mmol) of AgNO_2 is dissolved in 15ml of acetonitrile(CH_3CN). To this solution is added 3.69g(60.9mmol) of propylamine in drops using a syringe and the resulting solution is stirred at

room temperature for 1 hr. Following the stirring, the reaction mixture is filtered through a 0.2 μ m membrane filter. With the filtrate shield from light, solvent is completely evaporated under a reduced pressure for 3~4 hrs to afford colorless oil. $^1\text{H-NMR}$ spectrum is as follows:

$^1\text{H-NMR}(\text{CD}_3\text{OD}, \text{ppm}): 4.87 [\text{s}, 2\text{H}, \underline{\text{H}}_2\text{N-CH}_2], 2.77 [\text{t}, 2\text{H}, \text{N-CH}_2], 1.61 [\text{m}, 2\text{H}, \underline{\text{CH}}_2\text{CH}_3], 1.02 [\text{t}, 3\text{H}, \text{CH}_2\underline{\text{CH}}_3]$

[0037] 2) Synthesis of $\text{Au}(\text{NH}_2\text{Pr})_n(\text{CN})$ mixture($n = 1, 2, 3$ and 4)

[0038] To a 50ml round bottom Schlenk flask are added 1.0g(4.5mmol) of AuCN and 15ml of acetonitrile(CH_3CN). To this slurry is added an excessive amount of propylamine in drops using a syringe and stirred at room temperature for 1 hr. Following the stirring, the reaction mixture is filtered through a 0.2 μ m membrane filter. With the filtrate shield from light, excessive amine and solvent are completely evaporated under a reduced pressure to afford colorless solid matter.

Example 1:

[0039] 6.42g(3.0mol) of $\text{Ag}(\text{NH}_2\text{Pr})_n(\text{NO}_2)$, 0.0013g(0.0006mol) of $\text{Au}(\text{NH}_2\text{Pr})_n(\text{CN})$ (that are produced by production example) and

0.0021g(0.0006mol) of copper(II)2-ethylhexanoate are dissolved in 5.4ml of acetonitrile to afford a coating solution. This coating solution is then applied to a glass substrate by spin coating. Under a photomask, the resulting coating film is exposed to light by using Oriel 200W UV exposing system for 10 minutes. Thereafter, the exposed coating film is developed with acetonitrile to afford a metal alloy pattern. This pattern is reduced by immersing in 0.05M hydrazine solution, and then it is annealed at 200°C in vacuum for 2 minutes to afford a final metallic reflective film having a certain pattern.

[0040]Heat resistance and durability of the reflective film are measured by comparing decrease of reflectivity after pressure-cooking test. In this test, at the wavelengths of 480nm, 633nm and 700nm, reflectivities of test pieces that had been subjected to high-humidity state at 100°C for 120 minutes are compared with initial values. The results are shown in Table 1 below.

Example 2:

[0041]The procedure of Example 2 is conducted according to the same manner as in the above Example 1, except that palladium(II)acetate was

used instead of copper(II)2-ethylhexanoate. Heat resistance and durability of the reflective film are shown in Table 1 below.

Example 3:

[0042]The procedure of Example 3 is conducted according to the same manner as in the above Example 1, except that titanium (IV) isopropoxide is used instead of copper(II)2-ethylhexanoate. Heat resistance and durability of the reflective film are shown in Table 1 below.

Example 4:

[0043]The procedure of Example 4 is conducted according to the same manner as in the above Example 1, except that palladium(II)acetate is used instead of $\text{AuCN}-(\text{PrNH}_2)_n$. Heat resistance and durability of the reflective film are shown in Table 1 below.

Example 5:

[0044]The procedure of Example 5 is conducted according to the same manner as in the above Example 1, except that palladium(II)acetate and

titanium(IV)isopropoxide are used respectively instead of $\text{AuCN}-(\text{PrNH}_2)_n$ and copper(II)2-ethylhexanoate. Heat resistance and durability of the reflective film are shown in Table 1 below.

Example 6:

[0045]The procedure of Example 6 is conducted according to the same manner as in the above Example 1, except that dicarbonylcyclopentadienyl-ruthenium(II) dimer and $\text{AuCN}-(\text{PrNH}_2)_n$ are used instead of $\text{AuCN}-(\text{NH}_2\text{Pr})_n$ and copper(II)2-ethylhexanoate. Heat resistance and durability of the reflective film are shown in Table 1 below.

Example 7:

[0046]The procedure of Example 7 is conducted according to the same manner as in the above Example 1, except that dicarbonylcyclopentadienyl-ruthenium(II) dimer is used instead of $\text{AuCN}-(\text{PrNH}_2)_n$. Heat resistance and durability of the reflective film are shown in Table 1 below.

Exempl 8:

[0047]The procedure of Example 8 is conducted according to the same

manner as in the above Example 1, except that dicarbonylcyclopentadienyl-ruthenium(II) dimer and titanium(IV)isopropoxide are used instead of $\text{AuCN}(\text{PrNH}_2)_n$ and copper(II)2-ethylhexanoate. Heat resistance and durability of the reflective film are shown in Table 1 below.

Comparative Example 1:

[0048]In a $10\text{E}^{-6}\sim 10\text{E}^{-10}$ Torr vacuum chamber, into which Ar gas is flowing to a pressure of 3 mTorr, vapor deposition of Ag by sputtering method is performed until Ag film having thickness of 300nm is obtained while maintaining a temperature of the substrate at 50°C . Heat resistance and durability of the reflective film are measured according to the same manner as in the above Example 1, and the results are shown in Table 1 below.

Comparative Example 2:

[0049]6.42g(3.0mol) of $\text{Ag}(\text{NH}_2\text{Pr})_n(\text{NO}_2)$ is dissolved in 5.4ml of acetonitrile to afford a coating solution. This coating solution is then applied to a glass substrate by spin coating. The resulting coating film is exposed to light using Oriel 200W UV exposing system for 10 minutes. Thereafter, the

exposed coating film is developed with acetonitrile and reduced by immersing in 0.05M hydrazine solution to afford a substantially pure metal alloy film. Subsequently, the procedure of spin coating through reduction is repeated twice to afford a 3-layer metal alloy film. This 3-layer film is annealed at 200°C in vacuum to afford a final metallic reflective film. Heat resistance and durability of the reflective film are measured according to the same manner as in the above Example 1, and the results are shown in Table 1 below.

Table 1

No.	Metal (alloy) film (forming method)	Used organometallic compound		Initial R.I.* (480 nm) Decrease of R.I. (%)	Initial R.I.* (633 nm) Decrease of R.I. (%)	Initial R.I.* (700 nm) Decrease of R.I. (%)
Comp. Ex. 1	Ag(sputtering)	Ag		245 60.4	287 46.8	296 42.3
Comp. Ex. 2	Ag(SOM**)	AgNO ₂ ⁻ (PrNH ₂) _n		211 80.4	270 77.8	283 75.9
Ex. 1	AgAuCu(SOM)	AgNO ₂ ⁻ (PrNH ₂) _n	Au(CN)(PrNH ₂) _n	212 13.1	269 8.5	281 7.4
Ex. 2	AgAuPd(SOM)	AgNO ₂ ⁻ (PrNH ₂) _n	(CH ₃ CO ₂) ₂ Pd	203 32.8	267 35.2	279 34.9
Ex. 3	AgAuTi(SOM)	AgNO ₂ ⁻ (PrNH ₂) _n	Ti[OCH(CH ₃) ₂] ₄	90 21.8	152 29.8	161 29.4
Ex. 4	AgPdCu(SOM)	AgNO ₂ ⁻ (PrNH ₂) _n	(CH ₃ CO ₂) ₂ Pd	191 8.7	257 16.9	272 16.4
Ex. 5	AgPdTi(SOM)	AgNO ₂ ⁻ (PrNH ₂) _n	(CH ₃ CO ₂) ₂ Pd	162 38.5	236 40.6	256 40.8
Ex. 6	AgRuAu(SOM)	AgNO ₂ ⁻ (PrNH ₂) _n	[C ₅ H ₅ Ru(CO) ₂] ₂	167 19.0	258 29.4	272 29.4
Ex. 7	AgRuCu(SOM)	AgNO ₂ ⁻ (PrNH ₂) _n	[CH ₃ (CH ₂) ₃ CH(C ₂ H ₅)CO ₂] ₂ Cu	198 1.9	261 13.5	275 13.9
Ex. 8	AgRuTi(SOM)	AgNO ₂ ⁻ (PrNH ₂) _n	Ti[OCH(CH ₃) ₂] ₄	148 4.3	249 21.6	268 22.9

* R.I.: reflective index

** SOM: spin on metal

[0050]As shown in Table 1, although the initial reflectivity of the Ag reflective film obtained through sputtering according to Comparative example 1 is relatively high, decrease of reflectivity in the pressure cooking test is considerable, implying its poor heat-resistance and durability. Similarly, the Ag reflective film obtained through photoreaction according to Comparative example 2 exhibits high initial reflectivity, but the reflectivity significantly decreases in the pressure cooking test, implying that it is inferior to the inventive reflective films in terms of heat resistance and durability.

[0051]These results verify that the reflective films prepared by the use of the inventive composition of organometallic compounds have high reflectivity at short wavelength as well as long wavelength and that they are so excellent in heat resistance, durability and chemical stability that they can stand well against high temperature and moisture.

Example 9:

[0052]6.42g(3.0mol) of $\text{Ag}(\text{NH}_2\text{Pr})_n(\text{NO}_2)$, 0.0013g(0.0006mol) of $\text{AuCN}^-(\text{PrNH}_2)_n$ and 0.0021g(0.0006mol) of copper(II)2-ethylhexanoate are

dissolved in 5.4ml of acetonitrile to provide a coating solution. This coating solution is then applied to a glass substrate by spin coating. The resulting coating film is exposed to light using an Oriel 200W UV exposure system for 10 minutes. Thereafter, the exposed coating film is developed with acetonitrile and reduced by immersing in 0.05M hydrazine solution to afford a substantially pure metal alloy film. Subsequently, the procedure of spin coating through reduction is repeated twice to afford a 3-layer metal alloy film. This 3-layer film is annealed at 200°C in a vacuum to produce a final metallic reflective film. Adhesiveness, specific resistance and reflectivity of the reflective film are measured by 3M scotch tape test, 4 point probe test and nano spectrometer, respectively. The results are shown in Table 2 in comparison with those of the Ag reflective films obtained from Comparative examples 1 and 2.

Table 2

No.	Metal (alloy) film	Adhesiveness (%)	Specific resistance($\mu\Omega\cdot\text{cm}$)	Reflective index(700 nm)
Comp. Ex. 1	Ag(sputter)	100	2.2	296
Comp. Ex. 2	Ag(SOM)	40~50	7	283
Ex. 9	AgAuCu(SOM)	120	15	281

[0053]As shown in Table 2, the reflective film made from the inventive composition of organometallic compounds is highly improved in

adhesiveness, while the decrease in specific resistance and reflectivity is immaterial.

[0054]As stated above, by virtue of the present invention, silver alloy patterns can be obtained through a simplified manufacturing process, which patterns have enhanced heat resistance, adhesiveness and chemical stability. The inventive method may be applied to making a reflective film for LCD and metal wiring (gate, source, drain electrode) for flexible displays or flat panel displays, and further to CMP-free damascene processing and PR-free ITO film deposition.

[0055]Simple modifications and changes of the present invention by persons skilled in the art are considered to be encompassed by the scope of the present invention.